CY7C1041BN

256K x 16 Static RAM

Features

- **Temperature Ranges**
  - **— Commercial: 0°C to 70°C**
  - **— Industrial: –40°C to 85°C**
  - **— Automotive-A: –40°C to 85°C**
- **High speed**
  - **— t_{AA} = 15 ns**
- **Low active power**
  - **— 1540 mW (max.)**
- **Low CMOS standby power (L version)**
  - **— 2.75 mW (max.)**
- **2.0V Data Retention (400 μW at 2.0V retention)**
- **Automatic power-down when deselected**
- **TTL-compatible inputs and outputs**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **Available in Pb-free and non Pb-free 44-pin TSOP II and molded 44-pin (400-Mil) SOJ packages**

Functional Description

The CY7C1041BN is a high-performance CMOS static RAM organized as 262,144 words by 16 bits.

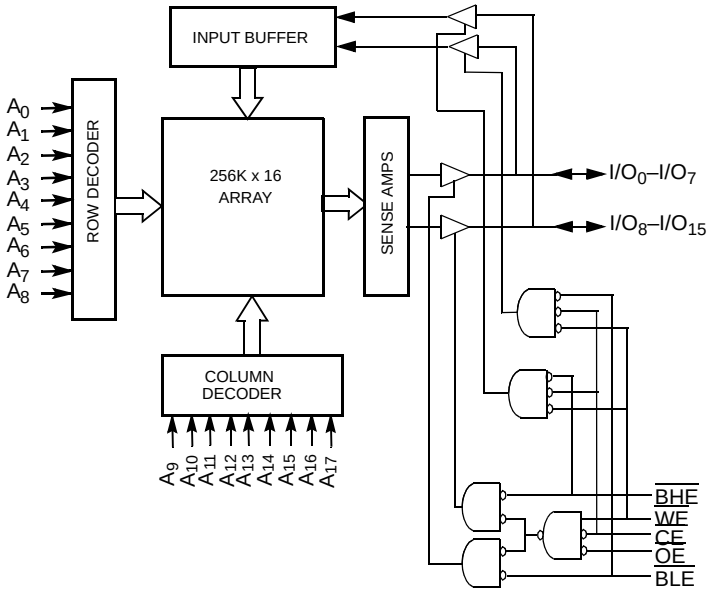
Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{17}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{17}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), the $\overline{BHE}$ and $\overline{BLE}$ are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

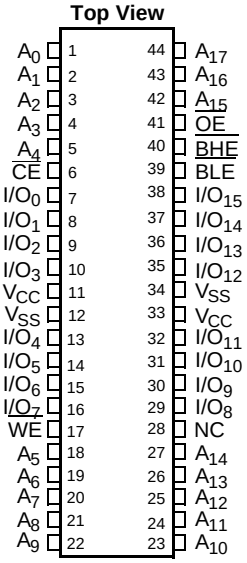
The CY7C1041BN is available in a standard 44-pin 400-mil-wide body width SOJ and 44-pin TSOP II package with center power and ground (revolutionary) pinout.

Logic Block Diagram



Pin Configuration

SOJ
TSOP II
Top View



Selection Guide

		-15	-20	Unit
Maximum Access Time		15	20	ns
Maximum Operating Current	Commercial	190	170	mA
	Industrial	210	190	
	Automotive-A		190	
Maximum CMOS Standby Current	Commercial	3	3	mA
	Commercial L	0.5	0.5	
	Industrial	6	6	
	Automotive-A		6	

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage on V_{CC} to Relative GND[1] .... –0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State[1] .....–0.5V to V_{CC} + 0.5V

DC Input Voltage[1] .....–0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA

Operating Range

Range	Ambient Temperature[2]	V_{CC}
Commercial	0°C to +70°C	5V ± 0.5
Industrial	–40°C to +85°C	
Automotive-A	–40°C to +85°C	

Electrical Characteristics Over the Operating Range

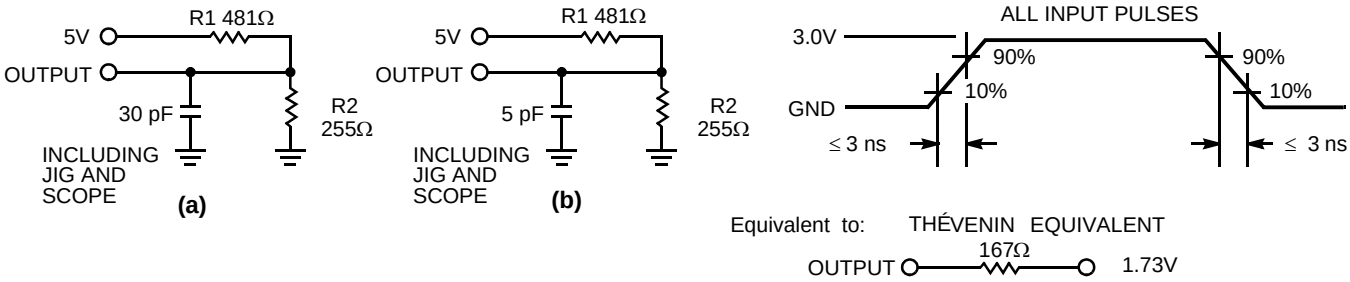
Parameter	Description	Test Conditions		-15 Min.	-15 Max.	-20 Min.	-20 Max.	Unit
V_{OH}	Output HIGH Voltage	V_{CC} = Min., I_{OH} = –4.0 mA		2.4		2.4		V
V_{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 mA			0.4		0.4	V
V_{IH}	Input HIGH Voltage			2.2	V_{CC} + 0.5	2.2	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage[1]			–0.5	0.8	–0.5	0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		–1	+1	–1	+1	mA
I_{OZ}	Output Leakage Current	GND ≤ V_{OUT} ≤ V_{CC}, Output Disabled		–1	+1	–1	+1	mA
I_{CC}	V_{CC} Operating Supply Current	V_{CC} = Max., f = f_{MAX} = $1/t_{RC}$	Comm'l		190		170	mA
			Ind'l		210		190	mA
			Auto-A				190	mA
I_{SB1}	Automatic CE Power-Down Current—TTL Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{IH}, V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}			40		40	mA
I_{SB2}	Automatic CE Power-Down Current —CMOS Inputs	Max. V_{CC}, $\overline{CE}$ ≥ V_{CC} – 0.3V, V_{IN} ≥ V_{CC} – 0.3V, or V_{IN} ≤ 0.3V, f = 0	Comm'l		3		3	mA
			Comm'l L		0.5		0.5	mA
			Ind'l		6		6	mA
			Auto-A				6	mA

Notes:
1. V_{IL} (min.) = –2.0V for pulse durations of less than 20 ns.
2. T_A is the case temperature.
3. Tested initially and after any design or process changes that may affect these parameters.

Capacitance[3]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 5.0V	8	pF
C_{OUT}	I/O Capacitance		8	pF

AC Test Loads and Waveforms



Switching Characteristics[4] Over the Operating Range

Parameter	Description	-15		-20		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{power}	V_{CC}(typical) to the First Access[5]	1		1		µs
t_{RC}	Read Cycle Time	15		20		ns
t_{AA}	Address to Data Valid		15		20	ns
t_{OHA}	Data Hold from Address Change	3		3		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		15		20	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		7		8	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z	0		0		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[6, 7]		7		8	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[7]	3		3		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[6, 7]		7		8	ns
t_{PU}	$\overline{CE}$ LOW to Power-Up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-Down		15		20	ns
t_{DBE}	Byte Enable to Data Valid		7		8	ns
t_{LZBE}	Byte Enable to Low Z	0		0		ns
t_{HZBE}	Byte Disable to High Z		7		8	ns

Notes:
4. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
5. This part has a voltage regulator which steps down the voltage from 5V to 3.3V internally. t_{power} time has to be provided initially before a read/write operation is started.
6. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
7. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.

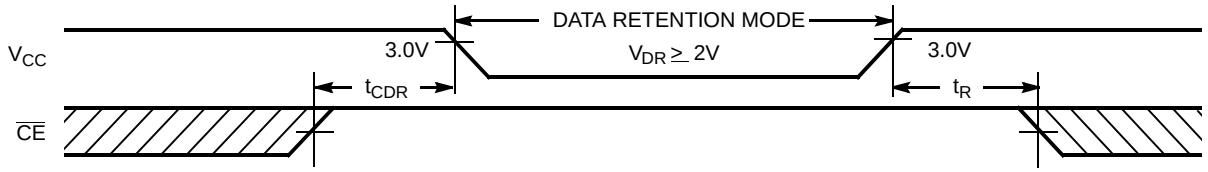
Switching Characteristics[4] Over the Operating Range (continued)

Parameter	Description	-15		-20		Unit
		Min.	Max.	Min.	Max.	
Write Cycle[8, 9]						
t_{WC}	Write Cycle Time	15		20		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	12		13		ns
t_{AW}	Address Set-Up to Write End	12		13		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	12		13		ns
t_{SD}	Data Set-Up to Write End	8		9		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[7]	3		3		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[6, 7]		7		8	ns
t_{BW}	Byte Enable to End of Write	12		13		ns

Data Retention Characteristics Over the Operating Range **(L version only)**

Parameter	Description	Conditions[11]	Min.	Max.	Unit
V_{DR}	V_{CC} for Data Retention		2.0		V
I_{CCDR}	Data Retention Current	$V_{CC} = V_{DR} = 2.0V$, $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$		200	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time		0		ns
t_R[10]	Operation Recovery Time		t_{RC}		ns

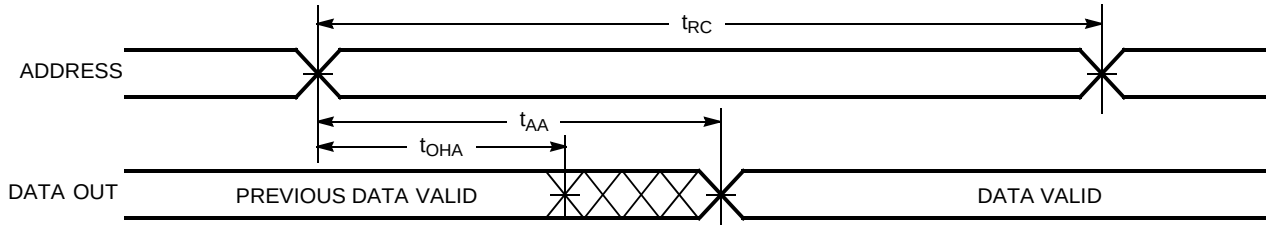
Data Retention Waveform



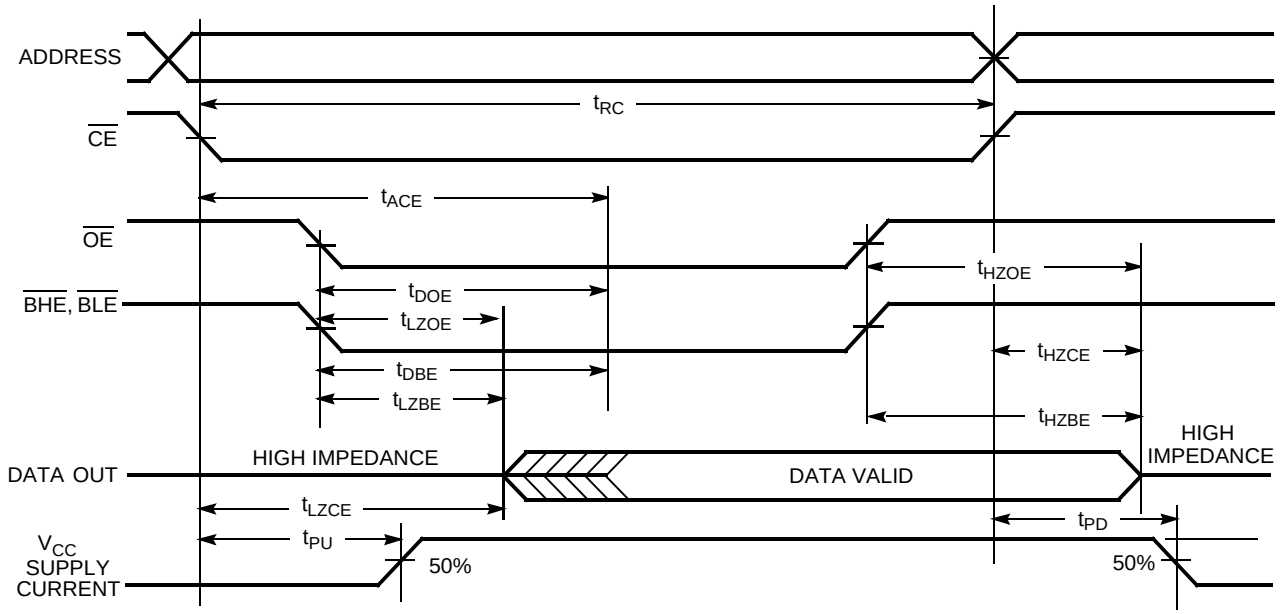
Notes:
8. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW, and $\overline{WE}$ LOW. $\overline{CE}$ and $\overline{WE}$ must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
9. The minimum write cycle time for Write Cycle no. 3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.
10. $t_r \leq 3$ ns for the -15 speed. $t_r \leq 5$ ns for the -20 and slower speeds.
11. No input may exceed V_{CC} + 0.5V.

Switching Waveforms

Read Cycle No. 1[12, 13]



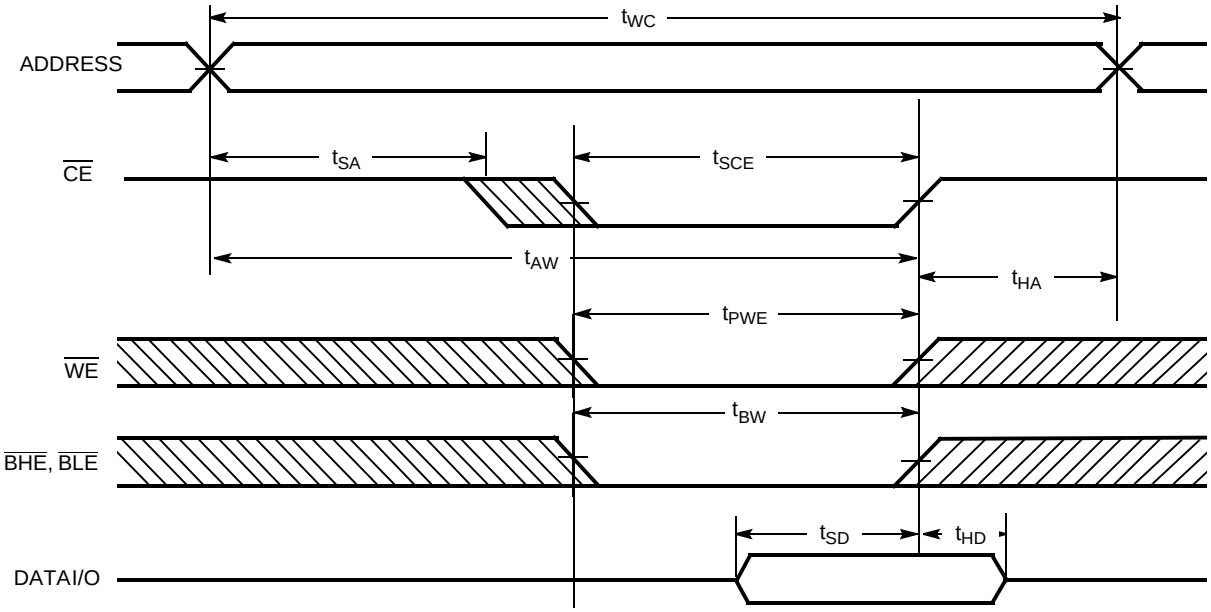
Read Cycle No. 2 ($\overline{OE}$ Controlled)[13, 14]



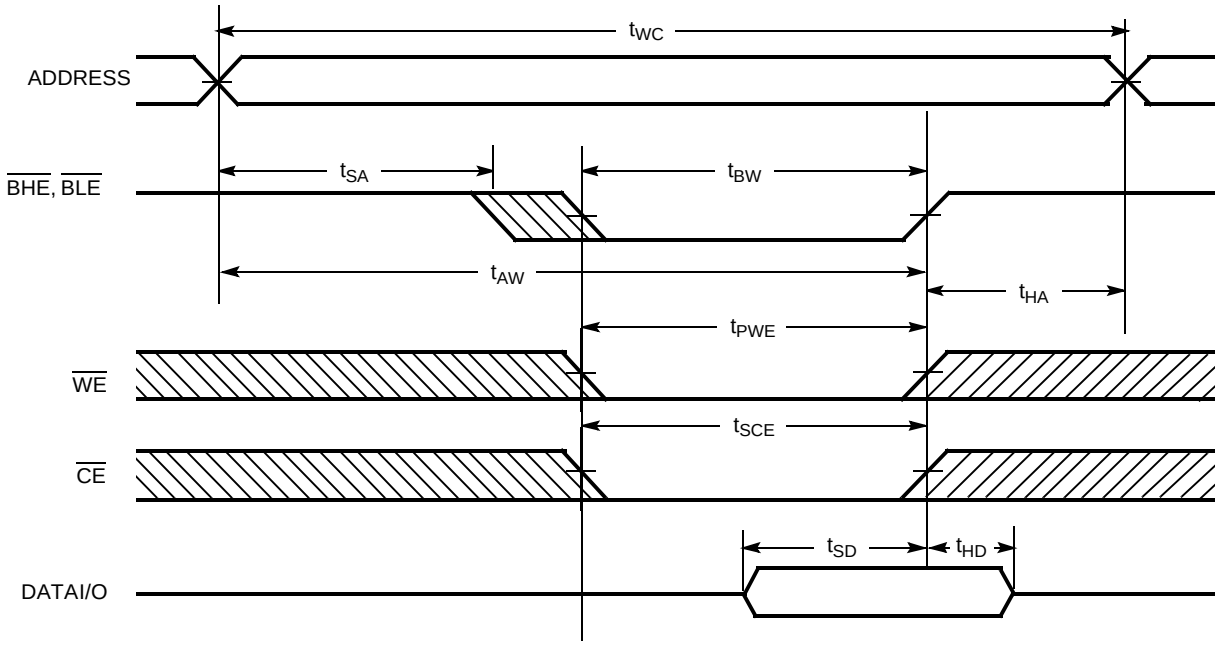
Notes:
12. Device is continuously selected. $\overline{OE}$, $\overline{CE}$, $\overline{BHE}$, and/or $\overline{BHE}$ = V_{IL}.
13. $\overline{WE}$ is HIGH for read cycle.
14. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{CE}$ Controlled)[15, 16]



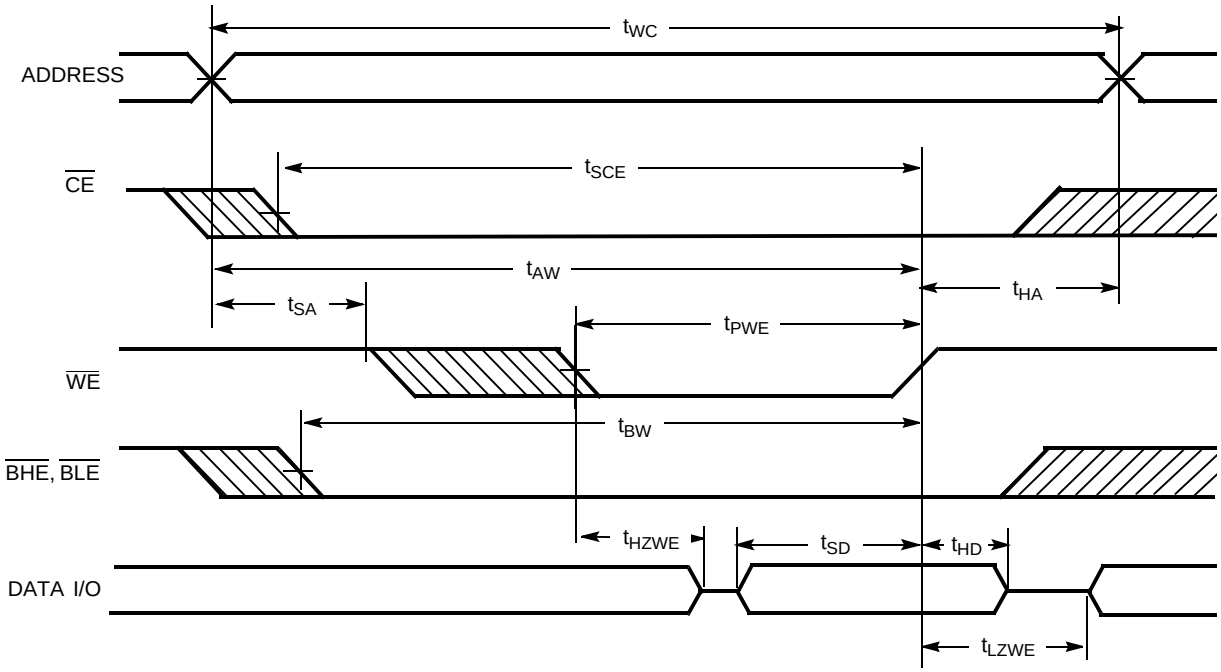
Write Cycle No. 2 ($\overline{BLE}$ or $\overline{BHE}$ Controlled)



Notes:
15. Data I/O is high impedance if $\overline{OE}$ or $\overline{BHE}$ and/or $\overline{BLE}$= V_{IH}.
16. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)



Truth Table

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	$\overline{BLE}$	$\overline{BHE}$	I/O_0–I/O_7	I/O_8–I/O_{15}	Mode	Power
H	X	X	X	X	High Z	High Z	Power Down	Standby (I_{SB})
L	L	H	L	L	Data Out	Data Out	Read All bits	Active (I_{CC})
L	L	H	L	H	Data Out	High Z	Read Lower bits only	Active (I_{CC})
L	L	H	H	L	High Z	Data Out	Read Upper bits only	Active (I_{CC})
L	X	L	L	L	Data In	Data In	Write All bits	Active (I_{CC})
L	X	L	L	H	Data In	High Z	Write Lower bits only	Active (I_{CC})
L	X	L	H	L	High Z	Data In	Write Upper bits only	Active (I_{CC})
L	H	H	X	X	High Z	High Z	Selected, Outputs Disabled	Active (I_{CC})

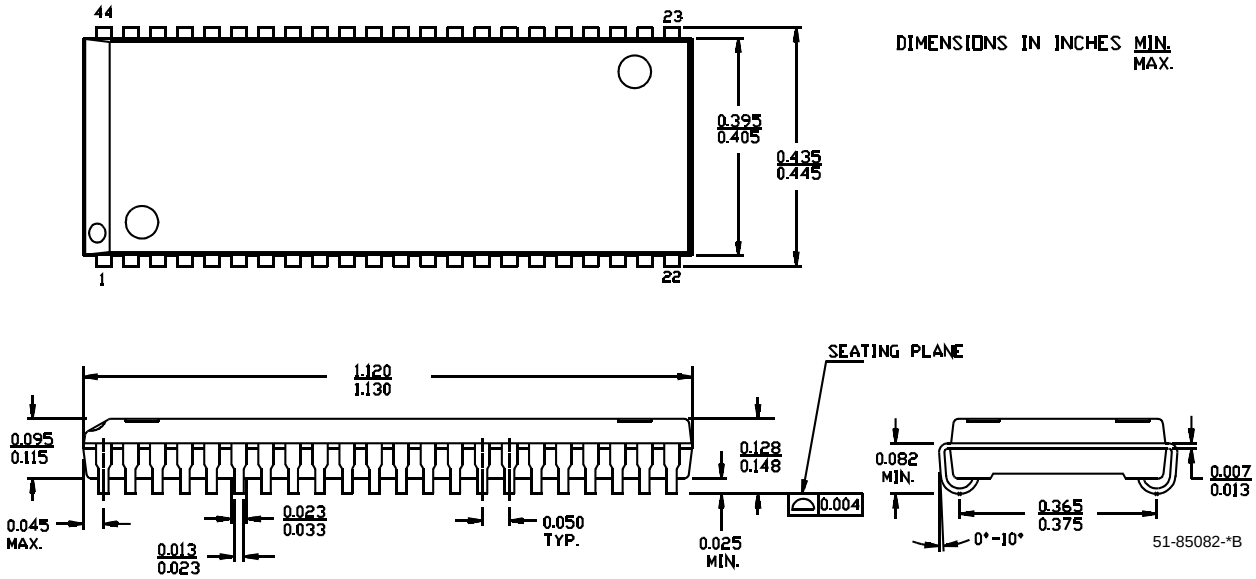
Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
15	CY7C1041BN-15VC	51-85082	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1041BN-15VXC		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1041BN-15ZC	51-85087	44-pin TSOP Type II	
	CY7C1041BN-15ZXC		44-pin TSOP Type II (Pb-free)	
	CY7C1041BNL-15ZC		44-pin TSOP Type II	
	CY7C1041BNL-15ZXC		44-pin TSOP Type II (Pb-free)	
	CY7C1041BN-15ZI		44-pin TSOP Type II	Industrial
	CY7C1041BN-15ZXI		44-pin TSOP Type II (Pb-free)	
	CY7C1041BN-15VI	51-85082	44-pin (400-Mil) Molded SOJ	
	CY7C1041BN-15VXI		44-pin (400-Mil) Molded SOJ (Pb-free)	
20	CY7C1041BN-20VXC		44-pin (400-Mil) Molded SOJ (Pb-free)	Commercial
	CY7C1041BNL-20VXC		44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1041BN-20ZC	51-85087	44-pin TSOP Type II	
	CY7C1041BN-20ZXC		44-pin TSOP Type II (Pb-free)	
	CY7C1041BN-20ZI		44-pin TSOP Type II	Industrial
	CY7C1041BN-20ZXI		44-pin TSOP Type II (Pb-free)	
	CY7C1041BN-20VXI	51-85082	44-pin (400-Mil) Molded SOJ (Pb-free)	
	CY7C1041BN-20ZSXA	51-85087	44-pin TSOP Type II	Automotive-A

Please contact local sales representative regarding availability of these parts.

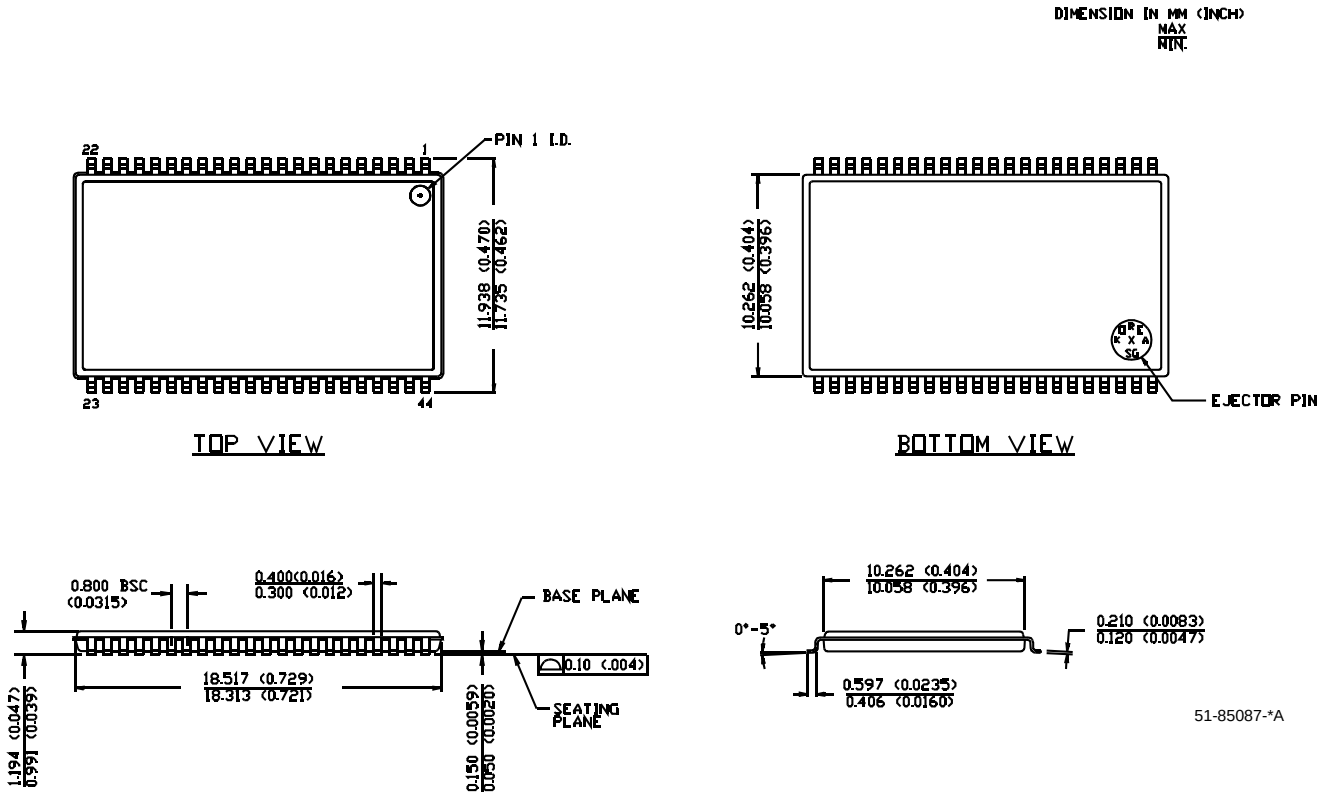
Package Diagrams

44-pin (400-Mil) Molded SOJ (51-85082)



Package Diagrams (continued)

44-Pin TSOP II (51-85087)



Document History Page

Document Title: CY7C1041BN 256K x 16 Static RAM Document Number: 001-06496				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	424111	See ECN	NXR	New Data Sheets
*A	498575	See ECN	NXR	Added Automotive-A operating range updated Ordering Information Table